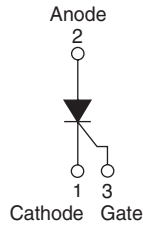


Surface Mountable Phase Control SCR, 16 A



D²PAK



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY

V_T at 16 A	< 1.25 V
I_{TSM}	300 A
V_{RRM}	800 V to 1600 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5	A
Aluminum IMS, $R_{thCA} = 15 \text{ °C/W}$	8.5	13.5	
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0	

Note

- $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
I_{RMS}		25	
V_{RRM}/V_{DRM}		800 to 1600	V
I_{TSM}		300	A
V_T	16 A, $T_J = 25 \text{ °C}$	1.25	V
dV/dt		500	V/μs
dI/dt		150	A/μs
T_J		- 40 to 125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} , AT 125 °C mA
VS-25TTS08SPbF	800	800	10
VS-25TTS12SPbF	1200	1200	
VS-25TTS16SPbF	1600	1600	

VS-25TTS...SPbF High Voltage Series



Vishay Semiconductors

Surface Mountable
Phase Control SCR, 16 A

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^\circ\text{C}$, 180° conduction half sine wave		16		A
Maximum RMS on-state current	I_{RMS}			25		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied		300		
		10 ms sine pulse, no voltage reapplied		350		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied		450		A^2s
		10 ms sine pulse, no voltage reapplied		630		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied		6300		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	16 A, $T_J = 25\text{ }^\circ\text{C}$		1.25		V
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$		12.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$			1.0		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.5		mA
		$T_J = 125\text{ }^\circ\text{C}$		10		
Holding current	I_H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$	-	100	
		VS-25TTS16		100	150	
Maximum latching current	I_L	Anode supply = 6 V, resistive load		200		
Maximum rate of rise of off-state voltage	dV/dt			500		$V/\mu s$
Maximum rate of rise of turned-on current	dI/dt			150		$A/\mu s$

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}			8.0	W
Maximum average gate power	$P_{G(AV)}$			2.0	
Maximum peak positive gate current	$+ I_{GM}$			1.5	A
Maximum peak negative gate voltage	$- V_{GM}$			10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$		60	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		45	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		20	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$		2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$		0.25	
Maximum DC gate current not to trigger	I_{GD}			2.0	mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$		0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$		4	
Typical turn-off time	t_q			110	



VS-25TTS...SPbF High Voltage Series

Surface Mountable
Phase Control SCR, 16 A

Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	240	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (SMD-220)	25TTS08S	
			25TTS12S	
			25TTS16S	

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W
For recommended footprint and soldering techniques refer to application note #AN-994

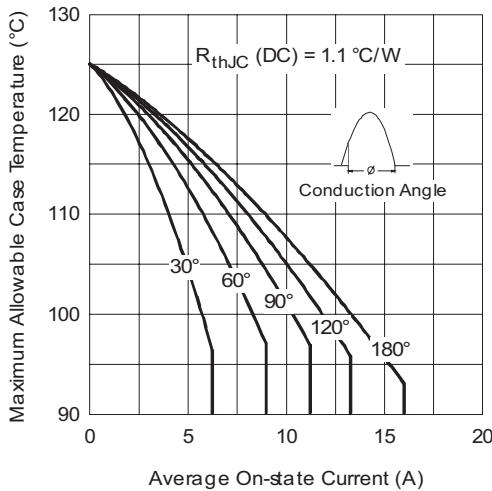


Fig. 1 - Current Rating Characteristics

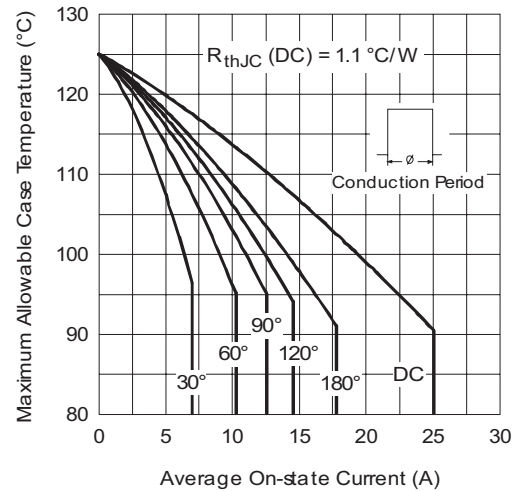


Fig. 2 - Current Rating Characteristics

VS-25TTS...SPbF High Voltage Series



Vishay Semiconductors

Surface Mountable
Phase Control SCR, 16 A

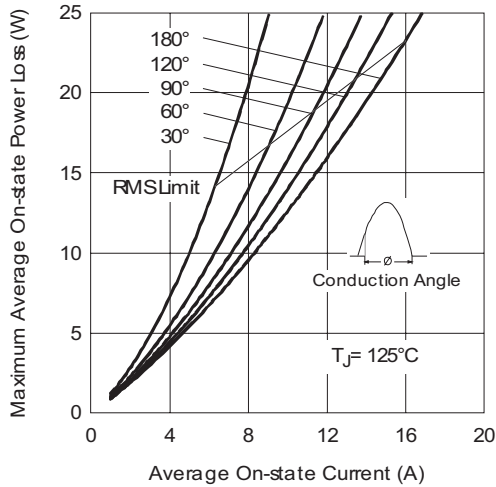


Fig. 3 - On-State Power Loss Characteristics

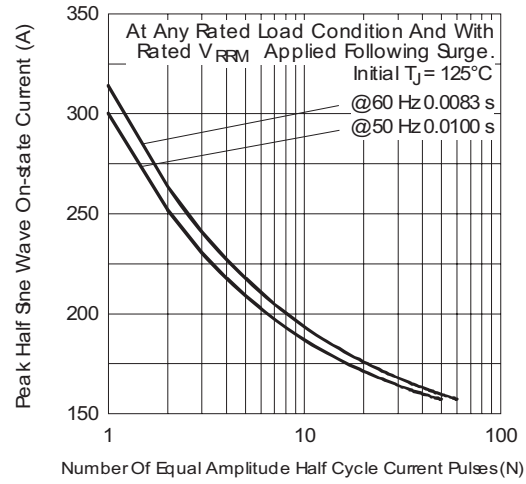


Fig. 5 - Maximum Non-Repetitive Surge Current

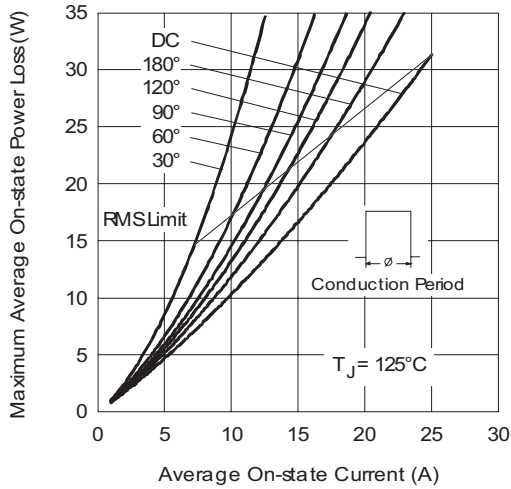


Fig. 4 - On-State Power Loss Characteristics

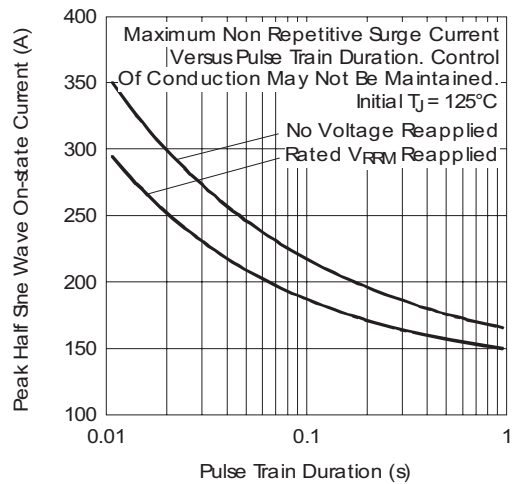


Fig. 6 - Maximum Non-Repetitive Surge Current

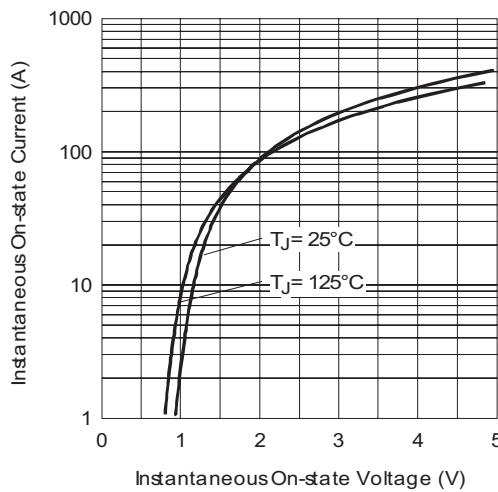


Fig. 7 - On-State Voltage Drop Characteristics



VS-25TTS...SPbF High Voltage Series

Surface Mountable
Phase Control SCR, 16 A

Vishay Semiconductors

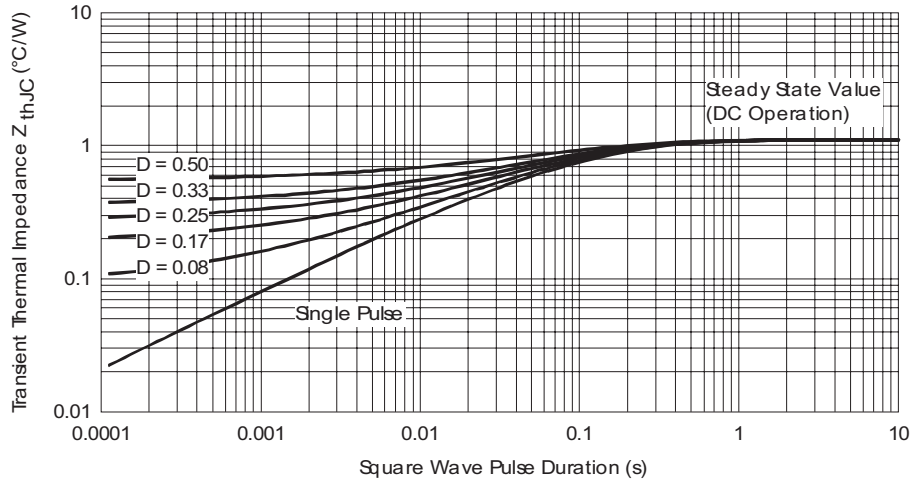


Fig. 8 - Gate Characteristics

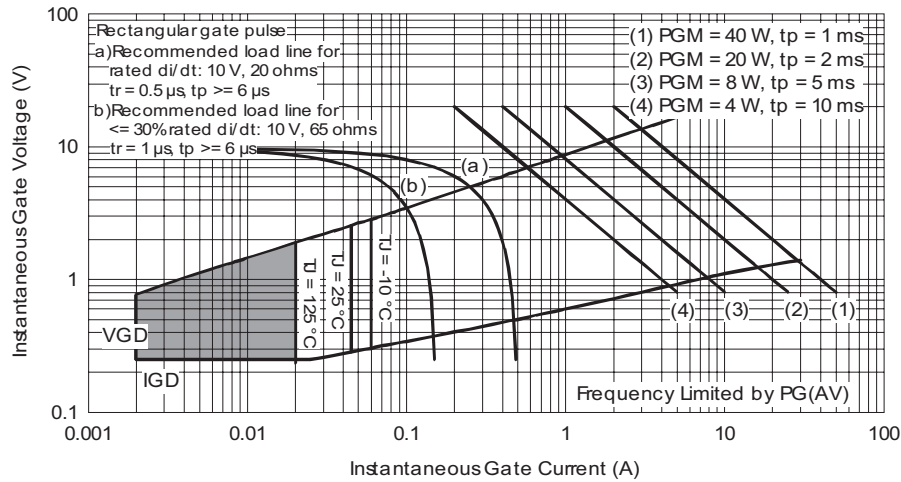


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

VS-25TTS...SPbF High Voltage Series



Vishay Semiconductors

Surface Mountable
Phase Control SCR, 16 A

ORDERING INFORMATION TABLE

Device code	VS-	25	T	T	S	12	S	TRL	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - HPP product suffix
- 2** - Current rating (25 = 25 A)
- 3** - Circuit configuration:
T = Single thyristor
- 4** - Package:
T = TO-220AC
- 5** - Type of silicon:
S = Standard recovery rectifier
- 6** - Voltage rating: Voltage code x 100 = V_{RRM}
- 7** - S = TO-220 D²PAK (SMD-220) version
- 8** -
 - None = Tube
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9** - PbF = Lead (Pb)-free

08 = 800 V
12 = 1200 V
16 = 1600 V

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC outline TO-263AB



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.